

# NVC6S5A354PLZ

## Power MOSFET

–60V, 100mΩ, –4A, P-Channel



ON Semiconductor®

www.onsemi.com

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

### Features

- 4V drive
- High ESD protection
- Low On-Resistance
- Pb-Free, Halogen Free and RoHS compliance

### Typical Applications

- Reverse Battery Protection
- High Side Load Switch

### SPECIFICATIONS

**ABSOLUTE MAXIMUM RATING** at  $T_a = 25^{\circ}\text{C}$  (Note 1)

| Parameter                                                                | Symbol         | Value       | Unit               |
|--------------------------------------------------------------------------|----------------|-------------|--------------------|
| Drain to Source Voltage                                                  | $V_{DS}$       | –60         | V                  |
| Gate to Source Voltage                                                   | $V_{GS}$       | $\pm 20$    | V                  |
| Drain Current (DC) (Note 2)                                              | $I_D$          | –4          | A                  |
| Drain Current (DC) (Note 3)                                              |                | –3          | A                  |
| Drain Current (Pulse)<br>$PW \leq 10\mu\text{s}$ , duty cycle $\leq 1\%$ | $I_{DP}$       | –16         | A                  |
| Power Dissipation<br>$T_a = 25^{\circ}\text{C}$ (Note 2)                 | $P_D$          | 1.9         | W                  |
| Power Dissipation<br>$T_a = 25^{\circ}\text{C}$ (Note 3)                 |                | 0.9         | W                  |
| Junction Temperature and<br>Storage Temperature                          | $T_j, T_{stg}$ | –55 to +175 | $^{\circ}\text{C}$ |

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE RATINGS

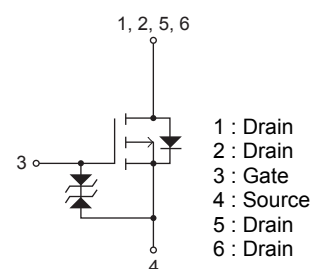
| Parameter           | Symbol          | Value | Unit                 |
|---------------------|-----------------|-------|----------------------|
| Junction to Ambient | $R_{\theta JA}$ | 78.1  | $^{\circ}\text{C/W}$ |
|                     |                 | 160   | $^{\circ}\text{C/W}$ |

Note 2 : Surface mounted on ceramic substrate(1500mm<sup>2</sup> × 0.8mm).

Note 3 : Surface mounted on FR4 board using a 92mm<sup>2</sup>, 1 oz. Cu pad.

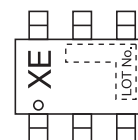
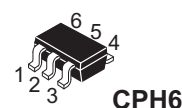
| $V_{DS}$ | $R_{DS(on)}$ Max | $I_D$ Max |
|----------|------------------|-----------|
| –60V     | 100mΩ @ –10V     | –4A       |
|          | 135mΩ @ –4.5V    |           |
|          | 145mΩ @ –4.0V    |           |

### ELECTRICAL CONNECTION P-Channel



- 1 : Drain
- 2 : Drain
- 3 : Gate
- 4 : Source
- 5 : Drain
- 6 : Drain

### MARKING



### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

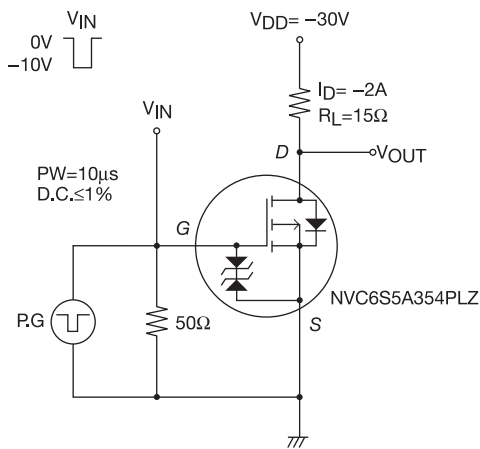
# NVC6S5A354PLZ

## ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 4)

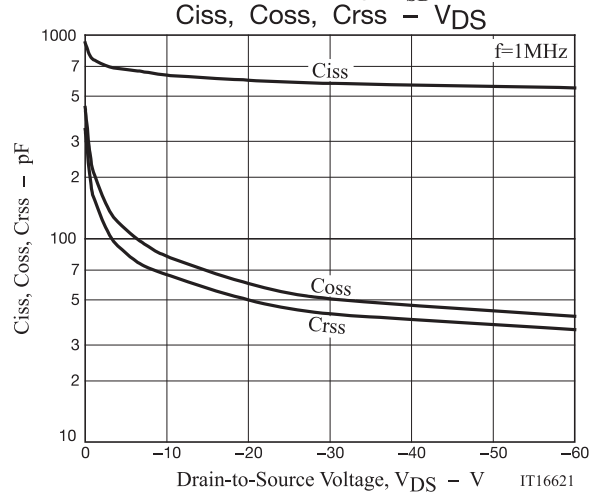
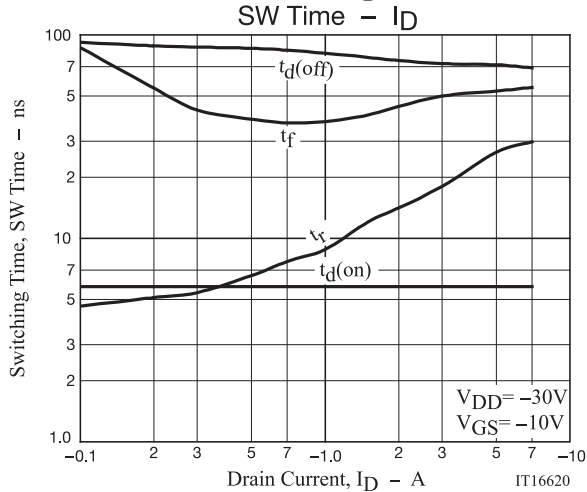
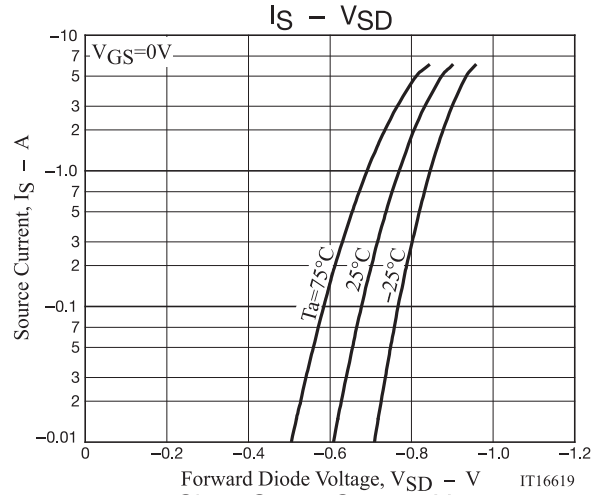
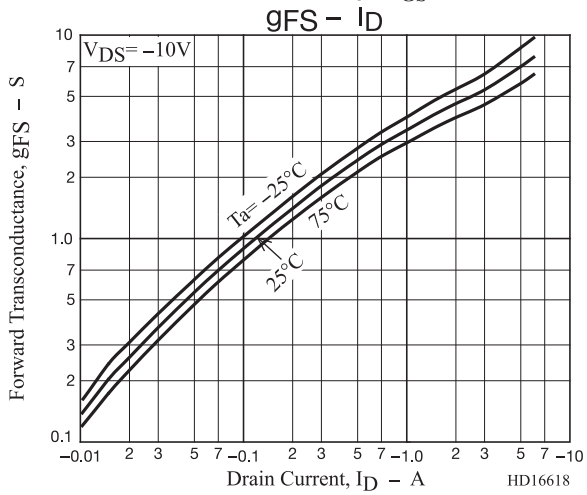
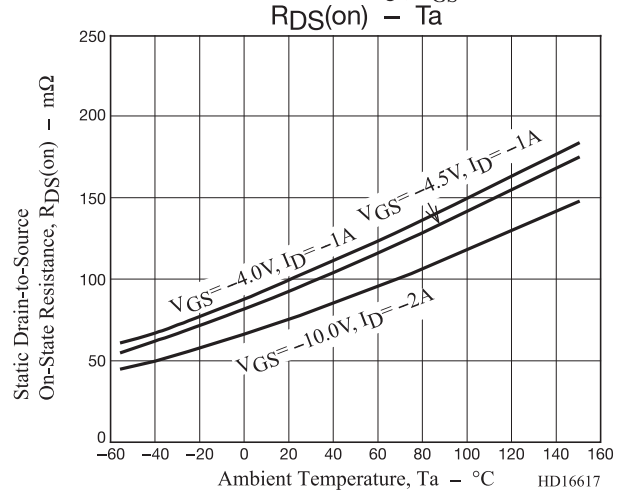
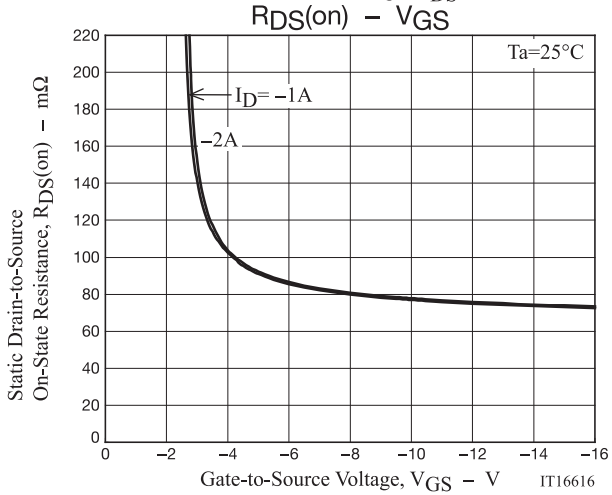
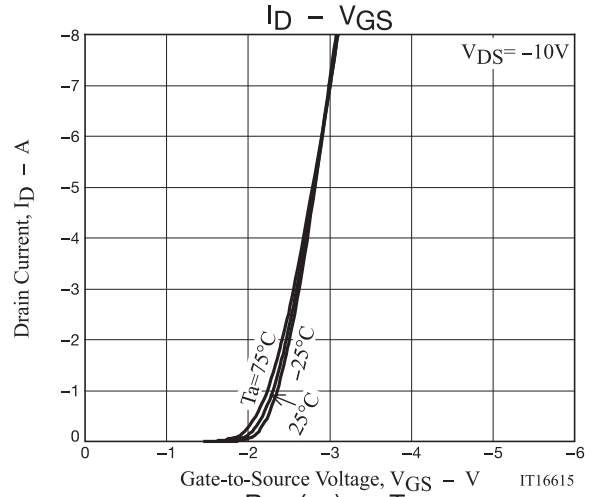
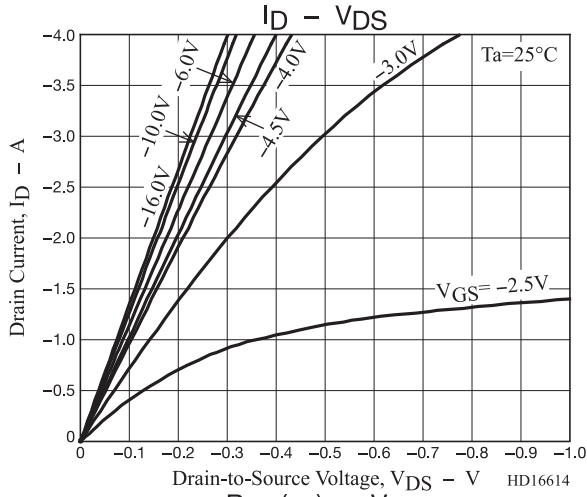
| Parameter                                  | Symbol              | Conditions                                                        | Value |       |      | Unit |
|--------------------------------------------|---------------------|-------------------------------------------------------------------|-------|-------|------|------|
|                                            |                     |                                                                   | min   | typ   | max  |      |
| Drain to Source Breakdown Voltage          | V(BR)DSS            | I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V                         | -60   |       |      | V    |
| Zero-Gate Voltage Drain Current            | I <sub>DSS</sub>    | V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V                        |       |       | -1   | μA   |
| Gate to Source Leakage Current             | I <sub>GSS</sub>    | V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V                        |       |       | ±10  | μA   |
| Gate Threshold Voltage                     | V <sub>GS(th)</sub> | V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA                       | -1.2  |       | -2.6 | V    |
| Forward Transconductance                   | g <sub>FS</sub>     | V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A                        |       | 4.8   |      | S    |
| Static Drain to Source On-State Resistance | R <sub>DS(on)</sub> | I <sub>D</sub> =-2A, V <sub>GS</sub> =-10V                        |       | 77    | 100  | mΩ   |
|                                            |                     | I <sub>D</sub> =-1A, V <sub>GS</sub> =-4.5V                       |       | 96    | 135  | mΩ   |
|                                            |                     | I <sub>D</sub> =-1A, V <sub>GS</sub> =-4V                         |       | 103   | 145  | mΩ   |
| Input Capacitance                          | C <sub>iss</sub>    | V <sub>DS</sub> =-20V, f=1MHz                                     |       | 600   |      | pF   |
| Output Capacitance                         | C <sub>oss</sub>    |                                                                   |       | 60    |      | pF   |
| Reverse Transfer Capacitance               | C <sub>rss</sub>    |                                                                   |       | 50    |      | pF   |
| Turn-ON Delay Time                         | t <sub>d(on)</sub>  | See Fig. 1                                                        |       | 5.8   |      | ns   |
| Rise Time                                  | t <sub>r</sub>      |                                                                   |       | 12    |      | ns   |
| Turn-OFF Delay Time                        | t <sub>d(off)</sub> |                                                                   |       | 78    |      | ns   |
| Fall Time                                  | t <sub>f</sub>      |                                                                   |       | 40    |      | ns   |
| Total Gate Charge                          | Q <sub>g</sub>      | V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A |       | 14    |      | nC   |
| Gate to Source Charge                      | Q <sub>gs</sub>     |                                                                   |       | 1.6   |      | nC   |
| Gate to Drain "Miller" Charge              | Q <sub>gd</sub>     |                                                                   |       | 3.4   |      | nC   |
| Forward Diode Voltage                      | V <sub>SD</sub>     | I <sub>S</sub> =-4A, V <sub>GS</sub> =0V                          |       | -0.84 | -1.2 | V    |

Note 4 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

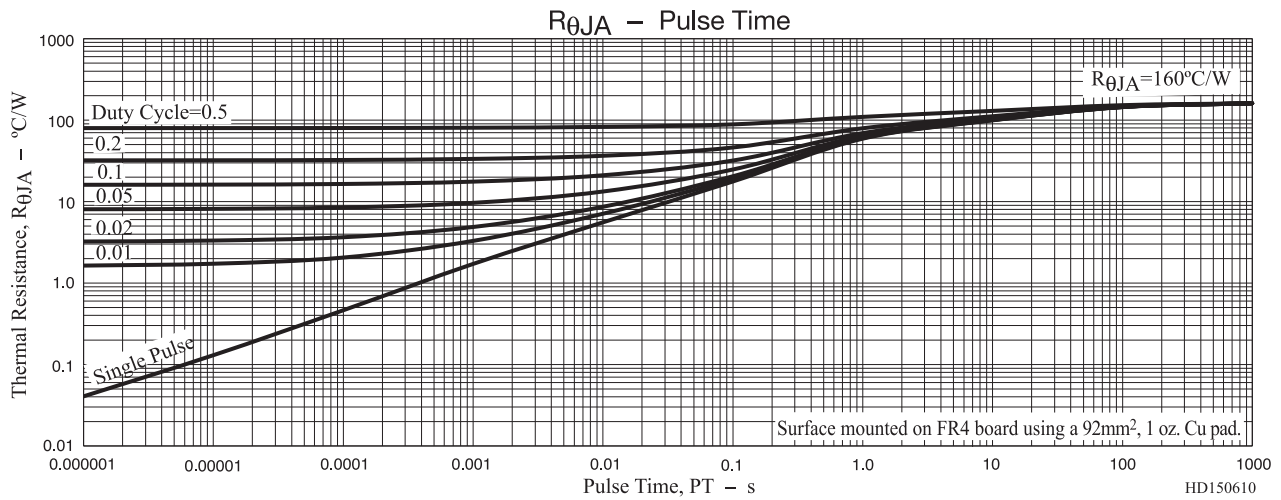
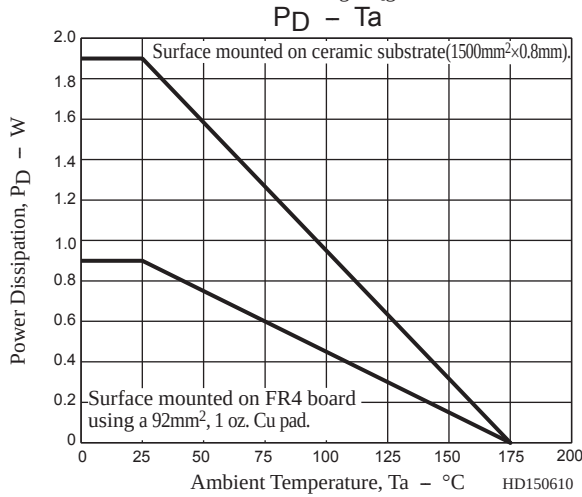
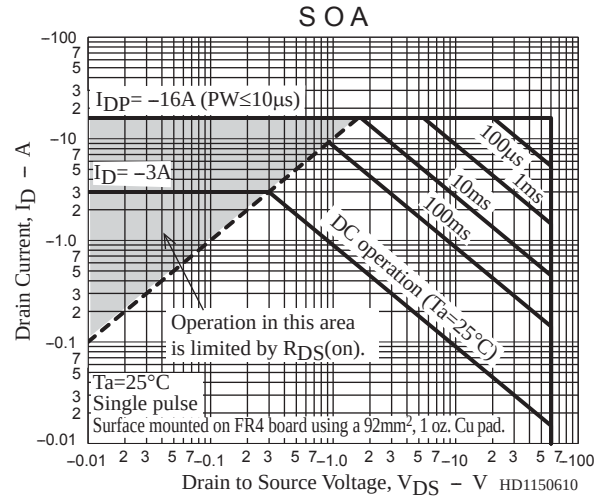
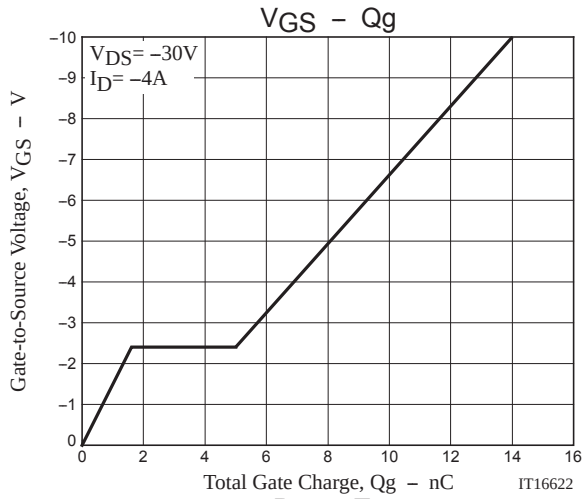
**Fig.1 Switching Time Test Circuit**



# NVC6S5A354PLZ



# NVC6S5A354PLZ



**NVC6S5A354PLZ**

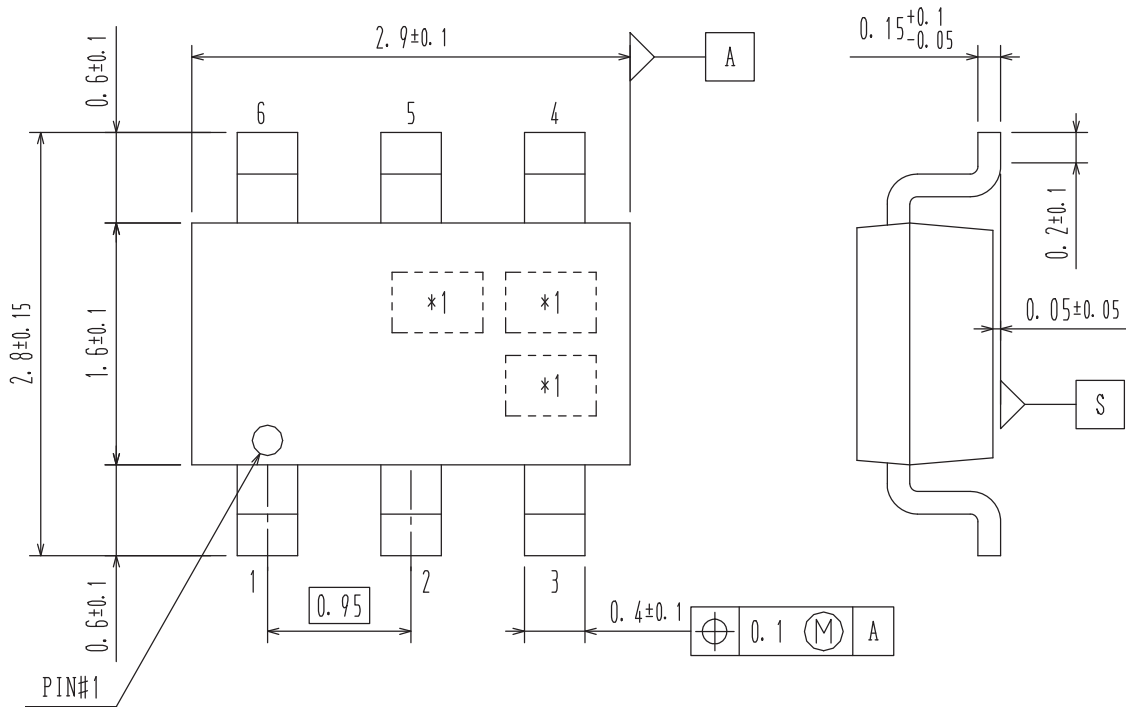
## PACKAGE DIMENSIONS

unit : mm

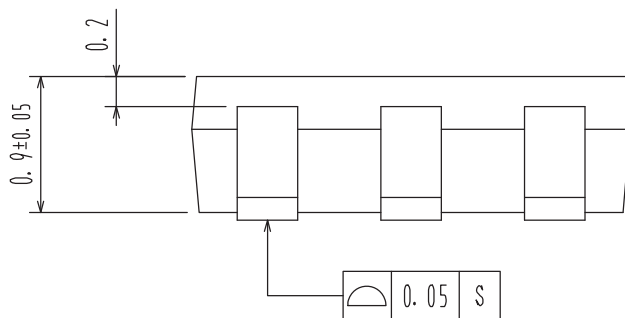
## CPH6

CASE 318BD

ISSUE 0

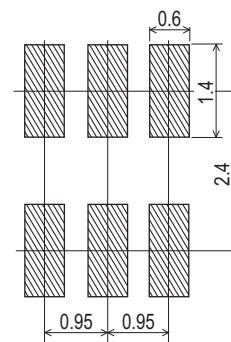


\*1: Lot indication



1 : Drain  
2 : Drain  
3 : Gate  
4 : Source  
5 : Drain  
6 : Drain

### Recommended Soldering Footprint



## NVC6S5A354PLZ

### ORDERING INFORMATION

| Device           | Marking | Package                          | Shipping (Qty / Packing) |
|------------------|---------|----------------------------------|--------------------------|
| NVC6S5A354PLZT1G | XE      | CPH6<br>(Pb-Free / Halogen Free) | 3,000 / Tape & Reel      |

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. [http://www.onsemi.com/pub\\_link/Collateral/BRD8011-D.PDF](http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF)

Note on usage : Since the NVC6S5A354PLZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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